INTRODUCTION

All noninteracting two-dimensional (2D) electronic systems in the thermodynamic limit are expected to exhibit an insulating ground state (1). This prevailing notion has been challenged only in the case where strong interactions dominate the electronic state notably in low-disorder, strongly interacting semiconductors, where an apparent transition to metallic conduction at low temperatures ($T_s$) has been observed (2, 3).

The physics gets more complex in the case where electronic correlations can lead to superconductivity. It is theoretically accepted that, in realistic 2D systems, with the unavoidable disorder and at a finite $T$, superconductivity exists only marginally and finite resistivity is always expected (4, 5). The value of this residual resistance is sensitive to the state of the system, and it usually depends exponentially on experimental variables such as $T$, magnetic field ($B$), measurement current ($I$), and the level of microscopic disorder. An exception is the case of exactly zero $B$, which can effectively be attained in experiments, where true superconductivity, with zero resistance at a finite $T$, is expected.

For these thin-film systems, the superconducting state can be markedly terminated with a transition to an insulating phase (6, 7). In this superconductor-insulator transition (SIT), metallic behavior is expected to be restricted to an unstable point at the transition ($\approx 4$). This point of view is often supported by experiments using a variety of ways to drive the SIT including thickness variation, disorder, $B$, and carrier concentration [for a review, see (9)].

There is, however, a growing number of independent studies (10–17) where the observation of an unexpected metallic state, intervening between the superconducting and insulating phases, has been reported. The unique characteristic attributed to this “anomalous metal” is that the superconducting transition, signaled by an exponential decrease below a well-defined critical $T$, $T_C$, of the sheet resistance ($R$) from its normal state value, $R_N$, is terminated, upon further cooling, with a crossover to a $T$-independent $R$ that persists down to the lowest $T$’s. This behavior, seen in thin films for which $R_N$ is substantially lower than the quantum of resistance $h/e^2 \approx 25.8 \Omega$, is observed over a wide range of experimental parameters and extends to relatively high $T$’s (18). Unlike ordinary metals, this state exhibits a vanishing Hall effect that was associated with a new particle-hole symmetric ground state (19, 20), its microwave response shows no cyclotron resonance, and it reveals the existence of short-range superconducting correlations (21).

The physical origin of this anomalous metallic state remains controversial, with experimental measurements variously interpreted as evidence of a Bose-metal phase (16) or dissipation arising from collective vortex tunneling (10, 15). Although several theoretical groups have addressed this state (19, 22–31), its robustness and ubiquitous nature pose difficulties in the development of a comprehensive model (18). The purpose of this article is to show that the apparent metallic behavior can result from an unforeseen sensitivity of these marginal superconductors to external perturbations.

RESULTS

Our data were obtained from two very different superconducting systems. The first is amorphous indium oxide (a:InO) thin film (Fig. 1, A and B), known for its high level of disorder reflected by high $R_N (<100 \Omega$) (32). The second system we investigated is made of sheets exfoliated from a single crystal of 2H-NbSe$_2$ (Fig. 1, C and D), which are of high purity and are characterized by low $R_N$ (<100 ohms) (32). Within the field of thin-film superconductors, these two systems represent opposite limits with respect to structure and disorder. Moreover, while 2H-NbSe$_2$ is a purely 2D superconductor having a thickness $d \ll \xi$, $\xi$ being the superconducting coherence length, $d$ of the a:InO films is approximately five times larger than its $\xi$ (33).

We begin by showing that the superconducting phase into which our samples transition at $T_C$ and which is interrupted as saturation sets in at lower $T$’s, is completely restored by introducing external low-pass filters into the measurement setup (see fig. S1). This is illustrated by plotting $R$ as a function of $T^{-1}$ obtained from an a:InO film (Fig. 1E) and a 2H-NbSe$_2$ film (Fig. 1F). In both samples, $R$ obtained from the unfiltered measurements (i.e., measured without additional external low-pass filters, red traces) initially decreases exponentially with an approximate activated behavior $R(T) \propto \exp(-U/B)k_B/T$, where $U(B)$ is the activation energy and $k_B$ is the Boltzmann constant. The exponential decrease then terminated with a transition to a saturated regime.
that persisted down to our lowest $T$’s. It is this saturated behavior of $R$ that was previously interpreted as indicating the novel metallic state (10, 15, 16, 18).

When we repeated the measurements, this time with additional low-pass filters installed (blue traces), we found that $R$ continued to follow the activated trend down to much lower $T$’s, and as $T$ was further lowered, $R$ continued to decrease to our noise level without saturating. The external low-pass filters effectively reduce the bandwidth of our measurements from 1 to 30 MHz (set by the twisted pairs of resistive measurement wires acting as low-pass resistor–capacitor filters) down to 200 to 300 kHz, depending on the specific setup (see, e.g., fig. S2). The lowest $R$ we now measure can exceed two orders of magnitude below the corresponding saturated values of the unfiltered measurements. We note that even with filtering, we continue to observe deviation from activated behavior in the lowest $T$ ranges measured. However, we believe that this results from imperfect filters. Additional measurements of a:InO film in a second fridge with improved low-$T$ filters show no deviation from activated behavior over the full range of achievable $T$’s (Fig. 2). We conclude that our data do not support the existence of quantum corrections (10, 15, 34) to the well-known transport due to thermally activated vortices (5).

Although the effect the filters have on both systems is qualitatively similar, it is important to point out that, while for a:InO it is only seen well below $T_C$ for 2H-NbSe$_2$, filtering has a measurable effect right from $T_C$ and at $B = 0$. In Fig. 3A, we show the thermodynamic superconducting-normal transitions of 2H-NbSe$_2$ at $B = 0$ in the left panel, and near $H_{c2}$ (the upper critical field terminating superconductivity) for several $T$’s in the right. The common theme in these figures is that a significant effect of the filters is measured very close to the transition into superconductivity. In contrast, for a:InO, initial differences between filtered and unfiltered measurements are only seen much below $T_C$. This is summarized in Fig. 3B, where we present the $B-T$ phase diagram for our samples. For 2H-NbSe$_2$, the initial effect of the filters, indicated by green triangles, overlaps within error with the superconductor-normal phase boundary (defined by $R = 0.9 \cdot R_N$), while for a:InO the filters significantly influence the results only well within the superconducting phase, indicated by blue and red triangles.

While filtering external radiation effectively eliminates the apparent metallic behavior, we found that saturation can be reintroduced by increasing the current used in our four-terminal measurements. For this purpose, we used both DC and AC currents ($I_{DC}$ and $I_{AC}$; see Materials and Methods) with similar results. The saturation induced
by increasing $I_{AC}$ is demonstrated in Fig. 4A, where we present data obtained from an a:InO film measured with filters at $B = 10$ T, using increasing levels of $I_0$ (the amplitude of $I_{AC}$). While at $I_0 = 1$ nA, the measured $V/I$, where $V$ is the voltage drop along the sample, followed an activated behavior with deviations that are barely noticeable over our noise level, for $I_0 \geq 50$ nA the data significantly deviated from its low-$I_0$ value and saturation set-in at low $T$’s, with the saturated value increasing with $I_0$. For reference, we include one trace (red) measured without filters and at $I_0 = 1$ nA, which exhibits the low-$T$ saturation. We note that, because $R$ is an equilibrium value defined by $\lim_{T \to 0} V/I$, the data presented in Fig. 4A strictly equal $R$ only in the ohmic regime ($I_0 \leq 1$ nA). Similar results are obtained while increasing $I_{DC}$ (see Fig. 4B, where we present data obtained from a 2H-NbSe$_2$ film).

When superconductors are subjected to strong enough $B$, their transport properties are dominated by vortex physics (5). Excessive $I$ can dislodge vortices, which are otherwise pinned at low $T$’s, inducing voltage and dissipation. The saturation induced in our experiment by increasing $I$ can therefore be attributed to heating. Under the application of a higher power ($P = I\cdot V$) by the measurement circuit, the electronic system is unable to equilibrate with its low-$T$ environment. This leads to an out-of-equilibrium steady state where the electrons are held at an elevated $T$, $T_{eff}$ higher than the surrounding $T$ (35). The $I$-induced deviations from activated behavior, as well as the saturation regions, can therefore be attributed to $T_{eff} > T$. We can self-consistently extract these $T_{eff}$’s by fitting the $R(T)$ data, obtained from the filtered measurements in the ohmic regime, with an activated form and then using this fit as our thermometry calibration curve: For each value of $V/I$, in the elevated $I$ measurements, we associate a $T_{eff}$ corresponding to $V/I = R$ in the calibration curve. Using this procedure, we conveniently define $T_{sat}$ as $T_{eff}$ in the $R$ saturation regime.

We now wish to suggest that the $R$ saturation observed in our unfiltered experiments, and which bears a notable resemblance to the $I$-driven saturation (see Fig. 4A), can also be associated with heating. While in this case the source of heating is less obvious, the fact that filtering the electrical lines connected to the sample effectively eliminates the saturation suggests that the culprit is ambient noise currents that propagate down the lines and couple directly to the low-$T$ electronic system. We can estimate the power density ($p$) delivered to the electronic system by these noise currents ($p_i$) by comparing $T_{sat}$ obtained during the application of known $p$ in our filtered, elevated $I$ measurements ($T_{sat}^{filtered}$) to the $T_{sat}$ obtained in the unfiltered, ohmic measurements ($T_{sat}^{unfiltered}$). To do this, we plot, in Fig. 4C, the $p$ dependence of $T_{sat}$ for two of our samples and use it as our $p$ meter. Red diamonds indicate $T_{sat}^{filtered}$ values corresponding to the unfiltered curves of each sample. We find $p_r = 1.8$ W/cm$^2$ for the a:InO sample and $8.2 \times 10^4$ W/cm$^2$ for the 2H-NbSe$_2$ sample.

Although our results show that our a:InO and 2H-NbSe$_2$ films do not exhibit an intermediate metallic phase, we cannot rule out the existence of such a phase in other superconducting systems for which a metallic state was previously reported (10, 15). We can, however, naively extend our effective-temperature analysis to these systems. In Fig. 4D, we present $T_{sat}$ versus $B$ obtained from our data (blue and green symbols), together with $T_{sat}$ values that we extracted from published data (black symbols). Whenever comparisons between results obtained from filtered and unfiltered measurements are not available (empty symbols), we fitted the data measured at higher $T$’s with activated behavior and used these fits as our thermometry calibration curves. This procedure, introduced in this context in (10), only provides a lower bound for $T_{sat}$ because the filtered measurements can also exhibit higher $U(B)$ (see fig. S3). While the data in Fig. 4D represent several very different systems, measured over a wide range of $T$’s, they all share a similar $B$ dependence: We found that $T_{sat} \approx \log(H_C/\alpha B)$, where $\alpha$ is a fit parameter of order 1, works reasonably well.

Before we proceed to discuss the implication of this simple elevated effective-temperature scenario, we wish to point out that there are other possible mechanisms that would lead to $I$-dependent transport in thin-film superconductor such as ours. Nonlinear vortex–related response may be relevant at finite $B$’s, and Berezinskii–Kosterlitz–Thouless vortex-antivortex unbinding may be at work at $B = 0$. At this stage, we are unable to rule out that these mechanisms play a notable role in the $I$ response of the system and may even lead to saturated, $T$-independent $R$ as $T \to 0$. We are not aware of a model that accounts for the stark difference between the results of the filtered and unfiltered measurements.

**DISCUSSION**

The data we present here show that the metallic behavior, often observed in thin-film superconductors, results from the exposure of the
superconducting phase to unwanted radiation or high $I$'s. While these can, in many cases, be eliminated, it is still worthwhile to consider why these superconductors so readily respond to excitations that leave other systems, under similar conditions (see the Supplementary Materials for further discussion), unaffected. We point out that $T_{\text{sat}}$ is routinely around a few kelvin, where it is unlikely that the cryogenic environment will limit the sample's ability to cool. Because the external power couples only to the electronic system, which exhibits an exponential $T$ dependence, it is reasonable to conclude that the observed sensitivity is a result of a bottleneck in the heat-transfer process that is between the electrons and the host phonons. This is not unexpected because in superconductors the electron condensate is decoupled from the heat-carrying phonons. If such a limiting mechanism is at play, a much more thorough theoretical analysis is necessary before we can go any further with quantitative tests.

In this study, we were able to compare two very different systems under virtually identical measurement conditions. It is reasonable to assume that, without filters, the radiation delivered to both types of samples would be the same. Unexpectedly, we find very different $p_r$'s. Similarly, their $T_{\text{sat}}$ values are different: ~0.4 K for a:InO and ~2 K for 2H-NbSe$_2$. If the effective-temperature picture is correct, we need to understand why two samples under similar external radiation end up responding in such a different manner. The reason, we believe, is rooted in the energy balance maintained by the electrons. Even if the radiation is the same, it is very likely that different systems will absorb this energy in different ways, reflecting the specific details of their electronic state. Compounding this are possible differences between the strength of the coupling to the phonon system to which the electrons can transfer the energy absorbed from the radiation. A detailed understanding of this scenario awaits further theoretical developments.

In summary, we showed that two very different thin-film superconductors are extremely sensitive to external perturbations and, in response to such perturbations, exhibit metallic-like, saturated $T$ dependence. We suggested two possible mechanisms: The first is based on

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**Fig. 4. Induced saturation and saturation $T$.** (A) $V/I$ versus $T^{-1}$ obtained from an a:InO film, measured at $B = 10$ T with increasing $I_0$'s. (B) $dV/dI$ versus $T^{-1}$ obtained from a 2H-NbSe$_2$ film, measured at $B = 2.3$ T with an increasing level of $I_0$ (see Materials and Methods). In both (A) and (B), we include one trace (red) measured, at our lowest $I$, without filters. (C) $T_{\text{sat}}$ versus $p$ extracted from the a:InO data presented in (A) (circles), and the 2H-NbSe$_2$ data presented in (B) (triangles), adopting the same color scale for the different $I$'s. The red symbols represent $T_{\text{sat}}$ extracted from the unfiltered measurements. The a:InO data include $I_0$'s left out of (A) for visibility. These curves are used as $p$ meters to estimate $p_r = 1.8$ and $8.2 \times 10^4$ W/cm$^3$ for the a:InO and 2H-NbSe$_2$ samples, respectively. (D) $T_{\text{sat}}$ versus $B$ evaluated for several samples. Our data are plotted in blue (a:InO) and green (2H-NbSe$_2$). The MoGe (10), Ta (11), and ZnCl$_2$ (15) data (black symbols) were extracted from the cited references. Full symbols represent data that were calculated using filtered measurements as a thermometer, while data plotted with empty symbols were estimated following the procedure in (10). All samples exhibit similar logarithmic $B$ dependence (see dashed black lines).
vortex pinning, and in the other, we assume that an overheated state exists, where the electronic system is unable to equilibrate with its surroundings. In the latter case, one should theoretically address not only the external power dissipated but also the heat flow away from the electronic system.

**MATERIALS AND METHODS**

In this work, we studied several different a:InO and 2H-NbSe₂ samples. Their relevant parameters are presented in Table S1. Details of the growth and fabrication were previously published [see (32) for 2H-NbSe₂ and (36) for a:InO].

The data presented in Fig. 2 were measured in a dilution refrigerator equipped with heavily filtered DC lines comprising feedthrough pi filters at room temperature, low-resistance twisted pairs (~8 ohms) from 300 to 4 K to reduce Johnson noise, lossy shielded twisted-pairs filters at room temperature, low-resistance twisted pairs (~8 ohms) tor equipped with heavily filtered DC lines comprising feedthrough pi capacitor-to-ground on the sampleholder. Furthermore, as thermometry below 0.1 K is delicate, a RuO₂ thermometer calibrated by Tamir

**SUPPLEMENTARY MATERIALS**

Supplementary material for this article is available at http://advances.sciencemag.org/cgi/content/full/5/6/eaa3826/DC1

**REFERENCES AND NOTES**


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Sensitivity of the superconducting state in thin films


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